

DESIGNING A HIGH POWER FACTOR SWITCHING PREREGULATOR WITH THE L4981 CONTINUOUS MODE

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The massive use of passive AC/DC off-line converters causes high harmonic content of line current and low power factor. This means higher pollution and higher energy consumption. To reduce these phenomena a improving line management, the standards IEC555 are to be introduced in Europe. An easy way to meet the standards is to perform the conversion in active mode.

INTRODUCTION

Conventional AC-DC converters usually employ a full wave rectifier bridge with a simple capacitor filter to draw power from the AC line. This "bulk" capacitor must be big enough to supply the total power during most of each half-cycle, while instantaneous line voltage is below the DC rectified voltage. Consequently, the line current waveform is a narrow pulse, and the power factor is poor (0.5-0.6) due to the high harmonic distortion of the current waveform.

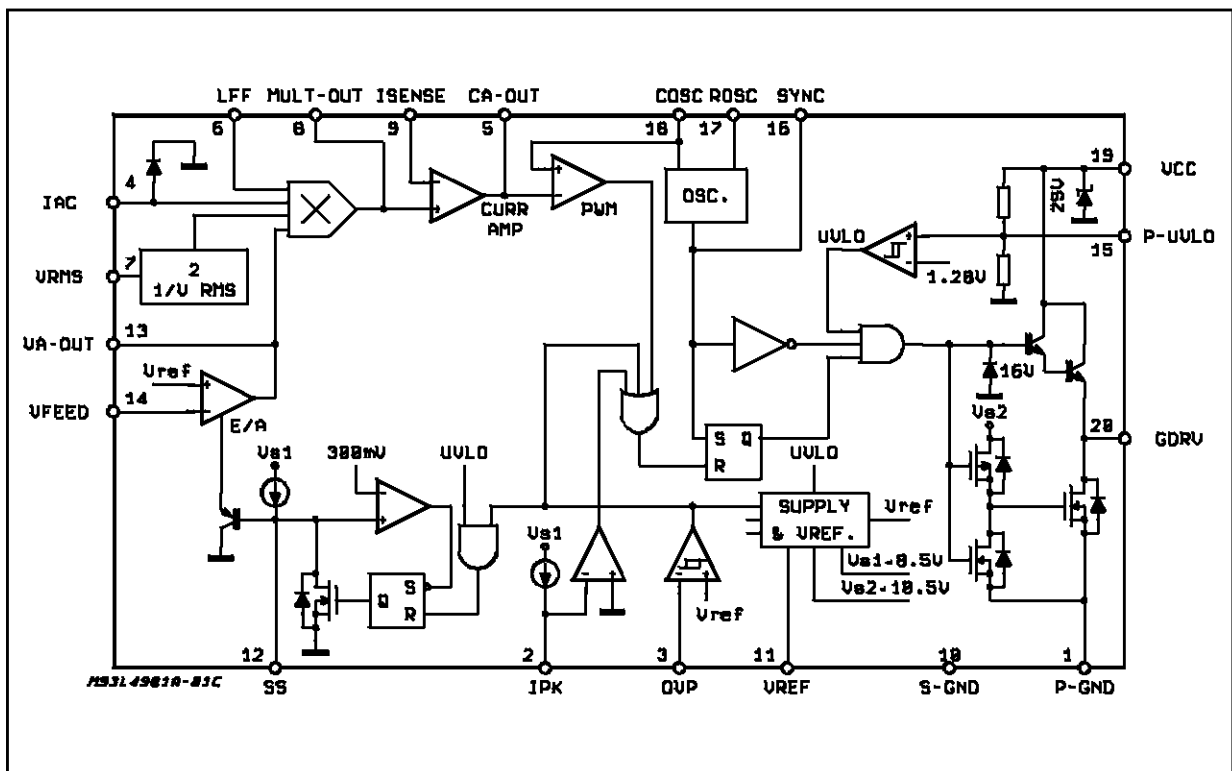
If a high power factor switching preregulator is interposed between the input rectifier bridge and the bulk filter capacitor, the power factor will be improved (up to 0.99). Increasing in addition, the

RMS current capability from the mains, reducing the bulk capacitor peak current and the harmonic disturbances.

Switching at a frequency much higher than the line's one, the preregulator draws a sinusoidal input current, in phase with the input line voltage.

There are several way that this can be accomplished. When the output voltage is higher than the input voltage ($V_o > V_{in}$), BOOST topology and continuous inductor current control mode are well suited to produce a good quality input sine current waveform. The input di/dt is low because the inductor is located between the bridge and the switch. This minimizes line noise and the line spikes will be absorbed by the inductor.

Figure 1: L4981 Block Diagram



APPLICATION NOTE

THE L4981 PFC CONTROLLER IC

The L4981 integrated circuit is a continuous mode average current controller with several specific functions for active power factor correction. It can operate in high quality, medium/high power conversion range and provides all the necessary features to achieve a very high power factor, up to 0.99. Thanks to the BCD technology used, operative switching frequency higher than 200kHz can be used.

The L4981 can be used in systems with universal input mains voltage without any line switch.

This new PFC offers the alternative of synchronization working at fixed frequency (L4981A), or working in modulated frequency (L4981B) to optimize the size of the input filter. Both devices control the conversion in average current mode PWM to maintain a sinusoidal line current without slope compensation.

MAIN FEATURES:

- Switching frequency higher than 200 kHz.
- Under Voltage Lockout with hysteresis and programmable turn-on threshold.
- Overvoltage and Overcurrent Protection.
- Precise (2%) on chip Reference externally available.
- Input/Output Synchronization (only for L4981A).
- Feed Forward Line and Load regulation.
- Universal input mains.
- Average current mode PWM.
- High Output Current totem pole driver.
- Low Start-up supply current.
- Soft Start.

P.F.C. BOOST TOPOLOGY OPERATION

The operation of the P.F.C. boost converter (see fig. 2) can be summarized in the following description.

The A.C. line voltage is rectified by a diode bridge and the rectified voltage delivered to the boost converter. The boost converter section, using a PWM switching technique, boosts the rectified input voltage to a D.C. controlled output voltage (V_O). The section consists of a boost inductor (L), a controlled power switch (Q), a boost diode (D), an output capacitor (C_O) and, obviously, a control circuitry.

Referring to the time-variable mains voltage (sine waveform), the converter produces a boost inductor average current like the rectified input voltage, changing continuously the duty-cycle of the active switch (Q).

The boosted D.C. voltage is controlled to a programmed value, higher than the maximum input instantaneous voltage (V_{IpK}).

Referring to the main currents shown in fig.2 schematic, the simplified formulae are (assuming: power efficiency = 1; output ripple voltage = 0; high frequency inductor ripple current = 0):

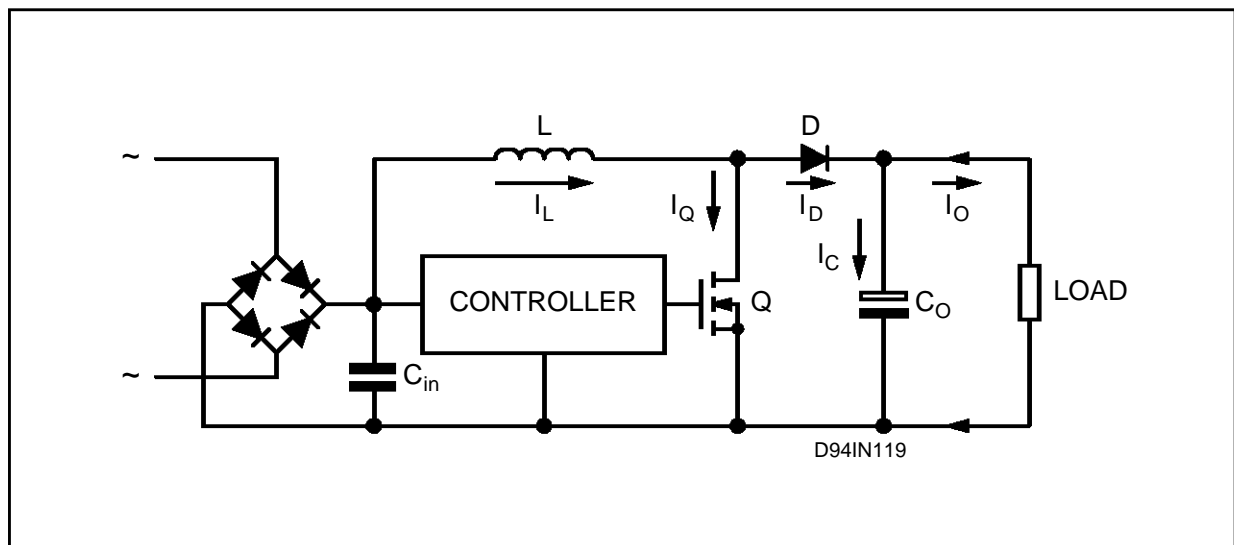
- 1) Peak inductor (L), switch (Q) and diode (D) currents

$$I_{Lpk} = I_{Qpk} = I_{Dpk} = 2 \sqrt{\frac{P_O}{V_{IpK}}}$$

- 2) RMS inductor current

$$I_{Lrms} = \sqrt{2} \sqrt{\frac{P_O}{V_{IpK}}}$$

Figure 2.



3) RMS switch current

$$I_{Qrms} = \frac{P_o}{V_{ipk}} \zeta / 2 \pm \frac{16 \zeta V_{ipk}}{3 \zeta \pi \zeta V_o}$$

4) Average diode current

$$I_{Davg} = I_o$$

5) RMS diode current

$$I_{Drms} = \frac{P_o}{V_{ipk}} \zeta / \frac{16 \zeta V_{ipk}}{3 \zeta \pi \zeta V_o}$$

6) Total RMS capacitor (C_o) current

$$I_c = I_o / \frac{16 \zeta V_o}{3 \zeta \pi \zeta V_{ipk}} \pm 1$$

7) RMS twice line frequency capacitor current

$$I_{c(2f)rms} = \frac{I_o}{\sqrt{2}}$$

8) RMS high frequency capacitor current

$$I_{c(hf)rms} = I_o / \frac{16 \zeta V_o}{3 \zeta \pi \zeta V_{ipk}} \pm 1.5$$

The figure 3 shows the above mentioned quantities, normalized to the D.C. output current (I_o), plotted versus V_{ipk} / V_o ratio. Moreover, the I_{Lpk} ζ I_{Lrms} normalized to I_o² value, related to the inductor energy (I² ζ L), is plotted in the diagram (dotted line). This last plot gives an idea on the heavy increase of the inductor size operating with large input voltage range.

Obviously, in real application the efficiency is less than 100% (η < 1). The output voltage ripple, related to the output capacitor (C_o) is a parameter to be considered. The inductor high frequency current ripple (ΔI_L) is another parameter affected by the inductor value (L), the switching frequency (f_{sw}) and the delivered power (P_o).

Figure 3.

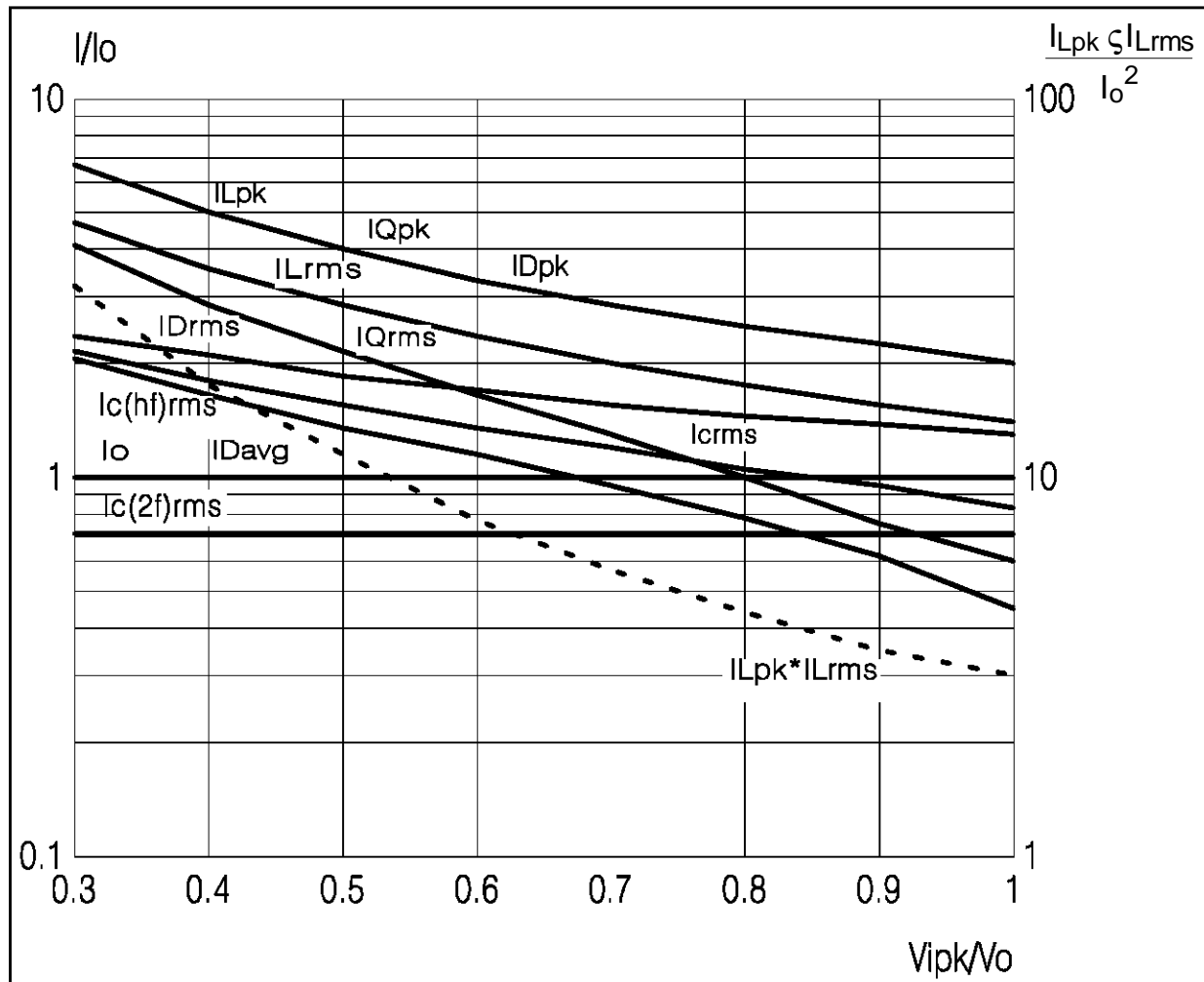
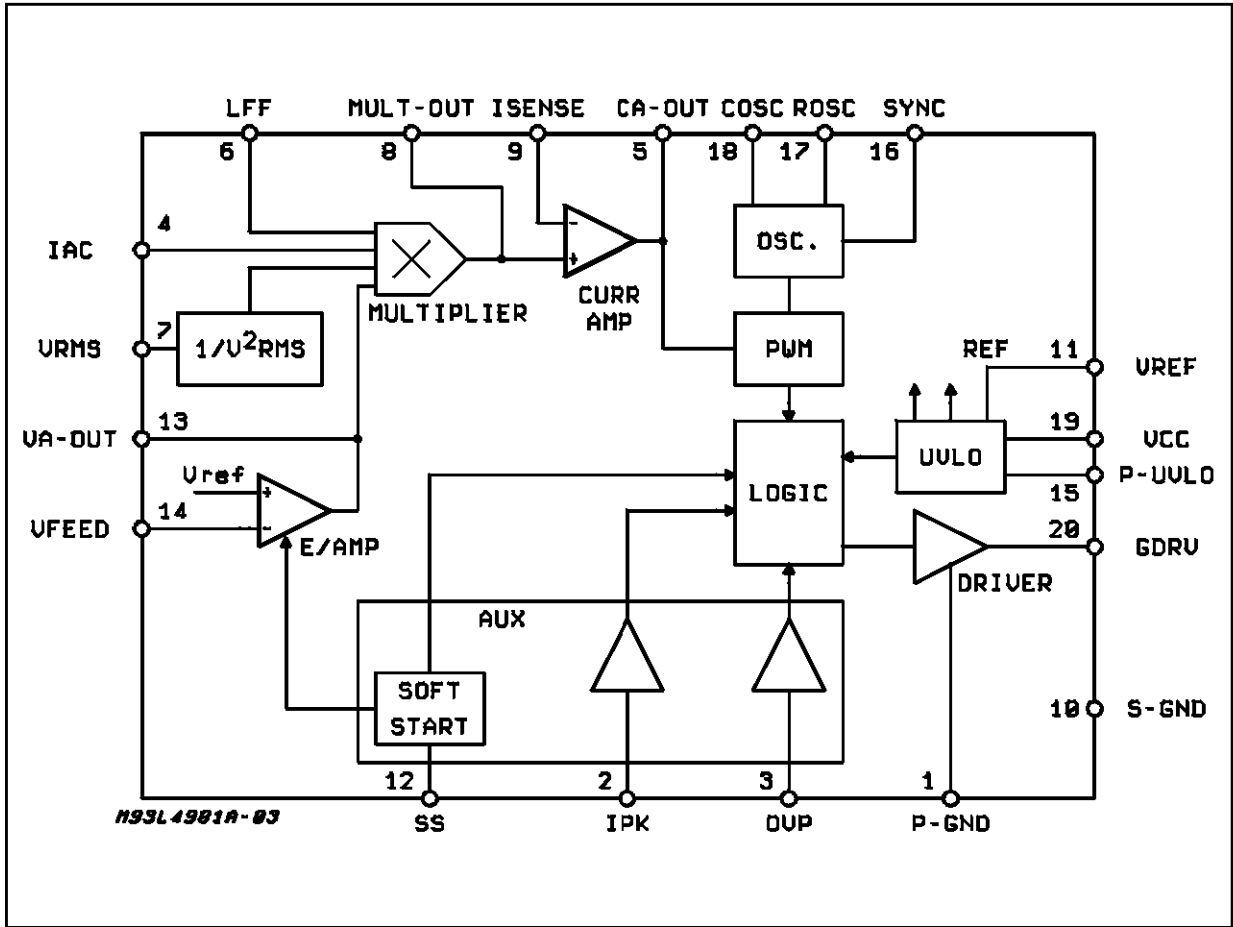


Figure 4.



CONTROLLER FUNCTION DESCRIPTION.

The L4981 I.C. controls the conversion process with a continuous mode average current method, using two control loops (current loop and voltage loop) see fig. 5. Moreover, several internal functions ensure high quality conversion performance. A description of the internal blocks will be detailed in the design criteria section and pin description. However, referring to fig. 4, here below a brief description of the main functions is done:

scription of the main functions is done:

Multiplier block.

This block produces an output current (programming current) as a product result of four different input signals (see fig. 13 for details). The multiplier output current, through a resistor connected to the negative side of a sense resistor, determines the error signal to the current loop.

Figure 5.

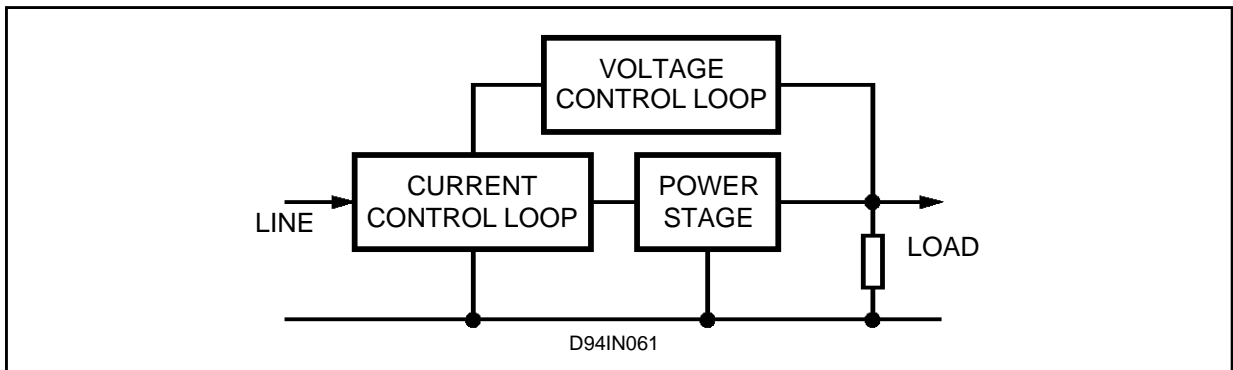
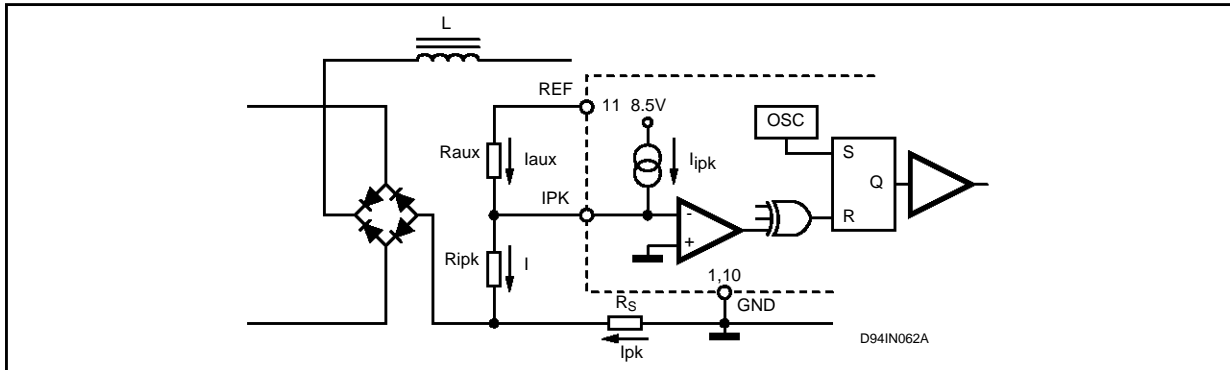


Figure 6.



Operational amplifier blocks.

Two amplifiers allow loop control. The first one (E/A), feeds back the output voltage (V_O) and delivers its output to the multiplier block. The second (C/A), feeds back the line current and produces the reference for the PWM section.

PWM block.

This block, comparing the sawtooth produced by the oscillator, with the reference signal from the C/A output, modulates its output signal duty-cycle. Its output, by the logic and driver sections, allows the controlled switch (Q) to modulate the inductor current.

Logic block.

Controls the flow from the PWM and the output with the Auxiliary function signals and soft start.

Driver block.

The driver supplies the gate current to turn on and off the power switch (Q). It delivers up to 1A peak current to allow high switching frequency applications.

Aux functions.

The Auxiliary functions allow to avoid overstress on power components of the application.

Power supply block.

This circuitry delivers the internal supply and references, recognizes the Undervoltage and Stand-by conditions to save consumption.

P.F.C. BOOST DESIGN CRITERIA

CONTROLLER DEVICE PIN DESCRIPTION AND BIASING CIRCUITRY.

Pin 1. P-GND (Power stage ground). This pin, on the pc-board, has to be connected close the external Mosfet source.

Pin 2. IPK (Overcurrent protection input). The current limitation is obtained with an internal comparator that holds down the output driver when the voltage at IPK input goes down to zero. In the L4981A, to preset the IPK input there is an internal current source (I_{ipk}) of typically 85 μA. The maximum peak current (I_{pk}) can be programmed connecting (see fig. 6) a single resistor (R_{ipk}) between this pin and the sense resistor (R_S):

$$R_{ipk} = \frac{R_S \zeta I_{ipk}}{I_{ipk}}$$

In the L4981B, to preset the IPK input, an auxiliary resistor (R_{aux}), connected from the VREF pin to the IPK pin, is required. The maximum peak current (I_{pk}) can be programmed choosing (see fig. 6) the resistances R_{aux} and R_{ipk}:

$$R_{ipk} = \frac{R_S \zeta I_{ipk}}{I_{aux}}$$

Where: $I_{aux} = \frac{V_{VREF}}{R_{aux}}$

Note: If used with the L4981A, the auxiliary resistor avoids that the current source spread affects the precision of the protection simply getting an auxiliary current (I_{aux}) much higher than I_{ipk}.

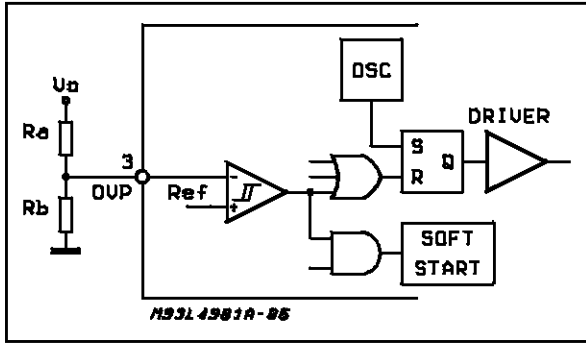
Pin 3. OVP (Overvoltage protection input). A comparator with a precise 5.1V reference voltage and 250mV of hysteresis, detects the overvoltage condition and turns the controller in stand-by condition (with low power consumption) and discharges the soft start capacitor. This pin (see fig. 7) has to be externally connected with a resistive divider (Ra and Rb) to the D.C. output voltage. The divider ratio is defined by the relation:

$$\frac{Ra}{Rb} = \frac{V_O + \Delta V_{OUT}}{5.1V} \pm 1$$

where: ΔV_{OUT} is the output overvoltage limit.

APPLICATION NOTE

Figure 7.

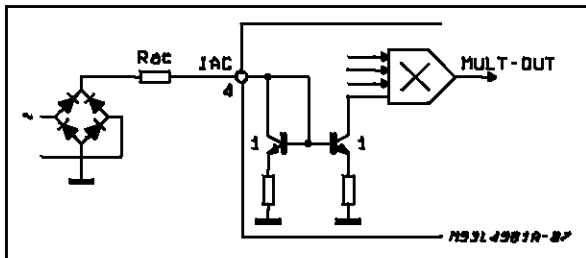


Pin 4. IAC (A.C. current input). This pin (see fig. 8) has to be connected through a resistor to the rectified line voltage to drive the multiplier with a current (I_{IAC}) proportional to the instantaneous line voltage:

$$I_{IAC} = \frac{V_l}{R_{ac}}$$

The relation between the input alternate current (I_{IAC}) and the output current (programming signal I_{mult}) of the multiplier is described at MULT-OUT section (pin8).

Figure 8.



Pin 5. CA-OUT (Current amplifier output). The CA_OUT delivers its signal to the PWM comparator. An external network (see fig. 9) defines the suitable loop gain to process the multiplier output and the line current signals. Before all, to avoid oscillation problem (see fig. 10) the maximum inductor current downslope ($V_{O/L}$) has to be lower than oscillator ramp-slope ($V_{srp} \zeta f_{sw}$):

$$\frac{V_o}{L} \zeta R_s \zeta G_{ca} \leq V_{srp} \zeta f_{sw}$$

where:

- V_{srp} is the oscillator ramp peak-peak voltage.
- G_{ca} is the current amplifier gain.
- f_{sw} is the switching frequency.

and rewritten as:

$$G_{ca} \leq \frac{V_{srp} \zeta f_{sw} \zeta L}{V_o \zeta R_s}$$

Figure 9.

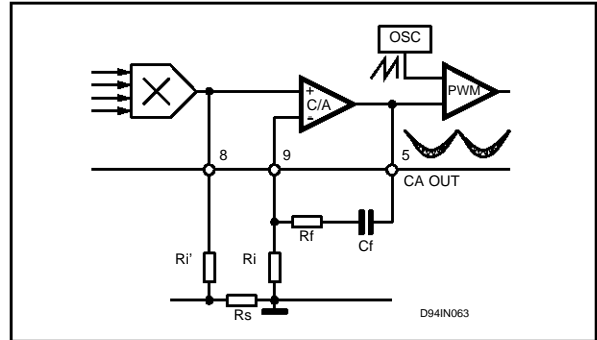
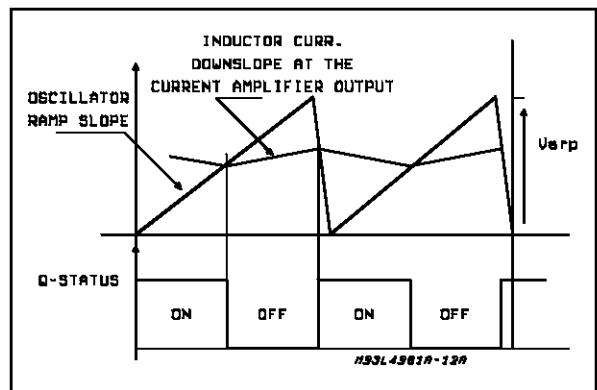


Figure 10.



defines the high frequency C/A gain ($1 + \frac{R_f}{R_i}$):

$$\frac{R_f}{R_i} \leq \frac{V_{srp} \zeta f_{sw} \zeta L}{V_o \zeta R_s} \pm 1$$

To define the C_f value, it's useful to consider the current open loop gain, defined by the ratio between the voltage across R_s and the current amplifier output signal:

$$G_{avg} = \frac{V_{rs}}{V_{ca}}$$

Because, in worst condition is:

$$V_{rs} = \frac{R_s \zeta V_o}{s \zeta L}$$

and the total variation of v_{ca} (the reference signal for PWM) is V_{srp} :

$$G_{avg} = \frac{R_s \zeta V_o}{V_{srp} \zeta 2\pi \zeta f \zeta L}$$

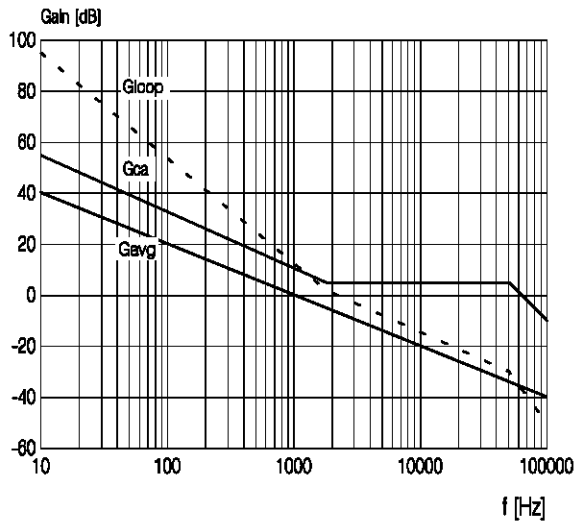
Multiplying this G_{avg} by G_{ca} and solving for the crossover frequency ($f = f_c$), follows:

$$f_c = \frac{f_{sw}}{2\pi}$$

To ensure a phase margin (higher than 45°), the zero frequency (f_z) should be about $f_c/2$, than:

$$f_z = \frac{f_{sw}}{4 \zeta \pi} = \frac{1}{2 \zeta \pi C_f \zeta R_f} \% \quad C_f = \frac{2}{R_f \zeta f_{sw}}$$

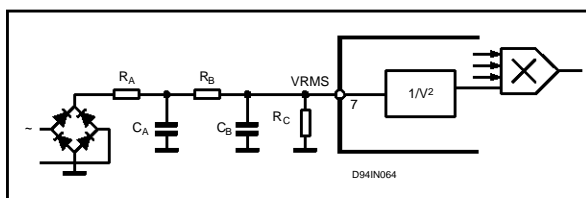
Figure 11.



Pin 6. LFF (Load feed-forward input). This voltage input pin allows to modify the multiplier output current proportionally to the load in order to improve the response time versus load transient. The control is working with V_{LFF} between 1.5V and 5.1V. If this function is not used, the LFF pin has to be connected to VREF pin. See also appendix A.

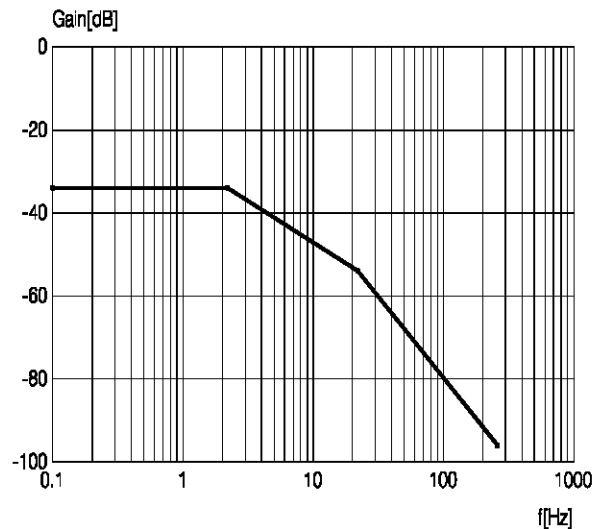
Pin 7. VRMS. Input to the divider ($1/V_{RMS}^2$), it is especially useful in universal mains applications to compensate the gain variation related to the input voltage change. It will be connected to an external network (see fig. 12a) giving a voltage level proportional to the mains V_{RMS} . The best control is reached using a VRMS voltage level in the range between 1.5V and 5.5V.

Figure 12a.



To avoid line current distortion, the rectified mains ripple (2f) level has to be reduced. A two pole filter, with three resistors and two capacitors, setting the lowest pole at 2Hz and the highest one at 13Hz, is enough to get the useful voltage level reducing to -80dB the 100Hz gain.

Figure 12b.



The signal (pin 7), with the network in fig. 12a is:

$$\begin{aligned} V_{RMS} &= 85V \text{ (110V -20\%)} & V_{RM(7)} &= 1.6V \\ V_{RMS} &= 260V \text{ (220V +20\%)} & V_{RM(7)} &= 5V \\ \text{Gain at } 2f(100\text{Hz}) & & & -80\text{dB} \end{aligned}$$

Pin 8. MULT-OUT (Output of the multiplier). This pin delivers the programming current (I_{mult}) according to the relation:

$$I_{mult} = 0.37 \zeta I_{AC} \zeta \frac{(V_{VA \pm OUT} \pm 1.28V) \zeta (0.8 \zeta V_{LFF} \pm 1.28V)}{V_{RMS}^2}$$

where: V_{VA-OUT} = E/A output voltage range

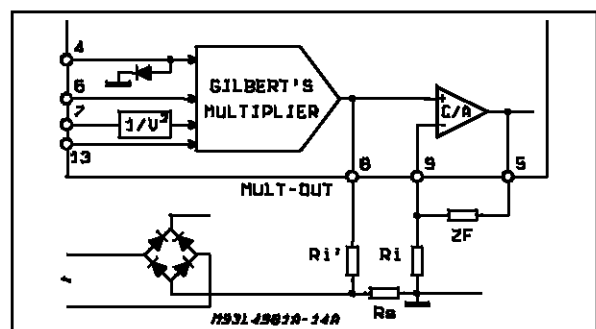
V_{LFF} = voltage input at pin 6

V_{RMS} = voltage input at pin 7

I_{AC} = input current at pin 4

To optimize the multiplier biasing for each application, the relation between I_{mult} and the other input signals to the multiplier are reported (see figures 13, 13a to 13h).

Figure 13.



APPLICATION NOTE

Figure 13a: MULTI-OUT vs. I_{AC} (V_{RMS} = 1.7V; V_{LFF} = 5.1V)

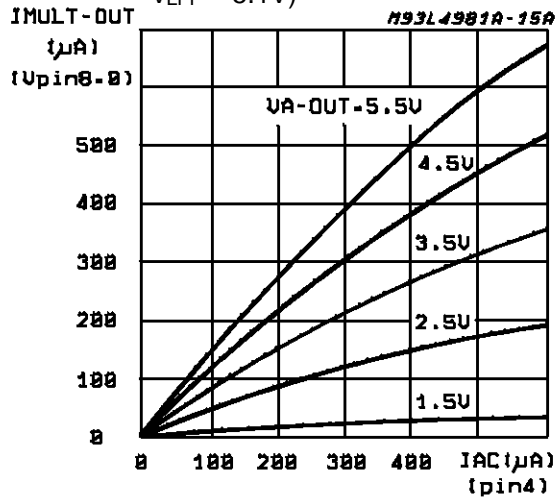


Figure 13b: MULTI-OUT vs. I_{AC} (V_{RMS} = 2.2V; V_{LFF} = 5.1V)

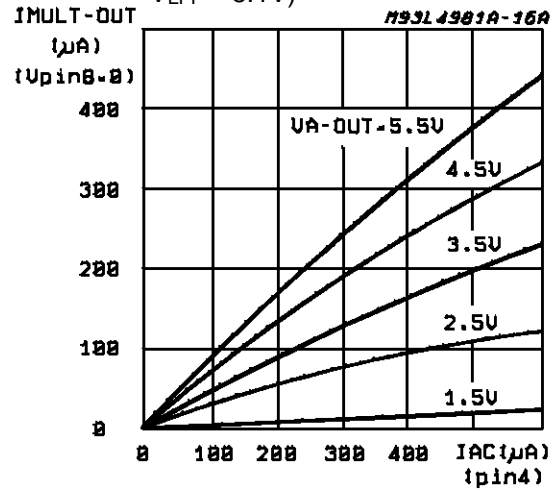


Figure 13c: MULTI-OUT vs. I_{AC} (V_{RMS} = 4.4V; V_{LFF} = 5.1V)

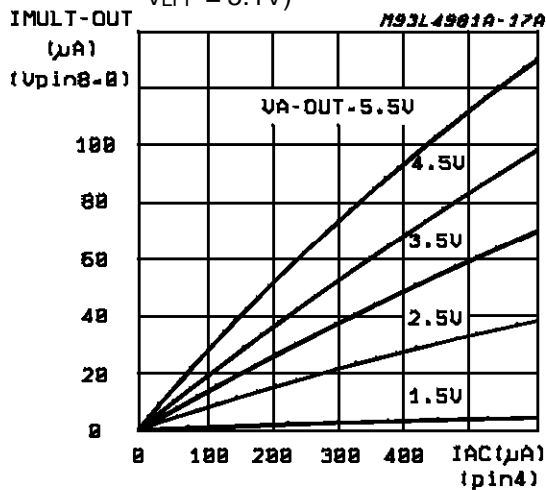


Figure 13d: MULTI-OUT vs. I_{AC} (V_{RMS} = 5.3V; V_{LFF} = 5.1V)

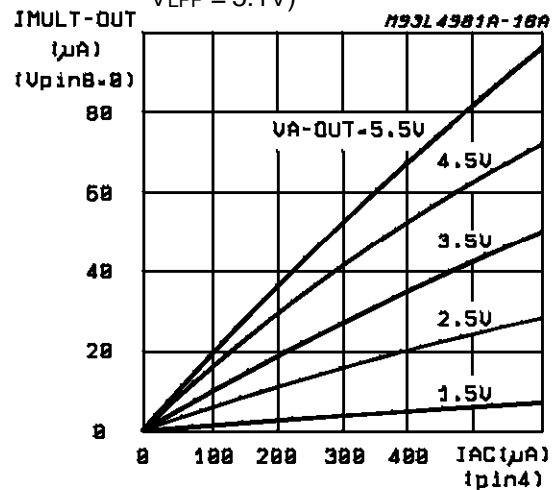


Figure 13e: MULTI-OUT vs. I_{AC} (V_{RMS} = 1.7V; V_{LFF} = 2.5V)

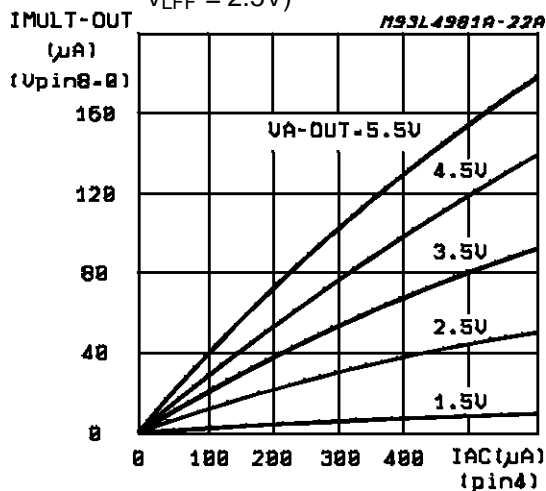


Figure 13f: MULTI-OUT vs. I_{AC} (V_{RMS} = 2.2V; V_{LFF} = 2.5V)

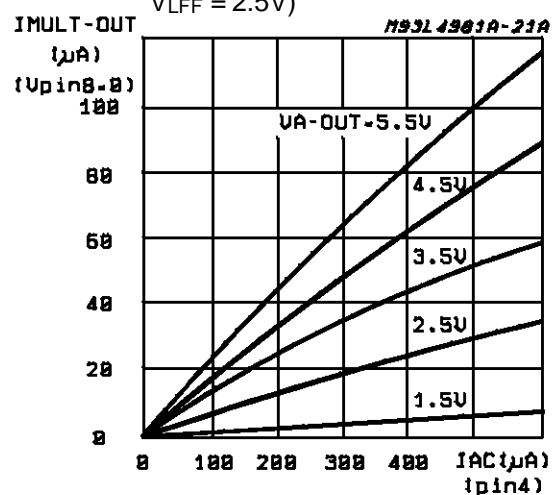


Figure 13g: MULTI-OUT vs. I_{AC} (V_{RMS} = 4.4V; V_{LFF} = 2.5V)

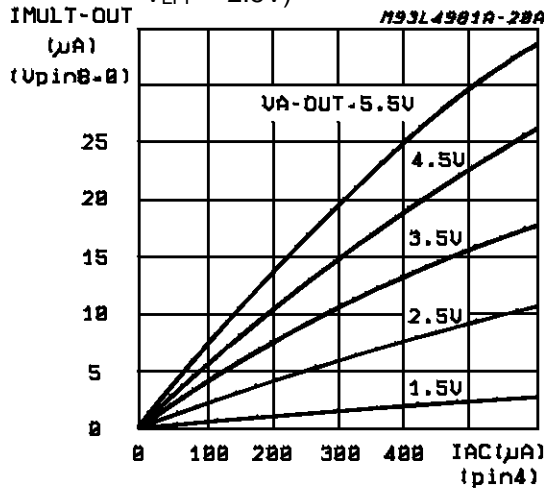
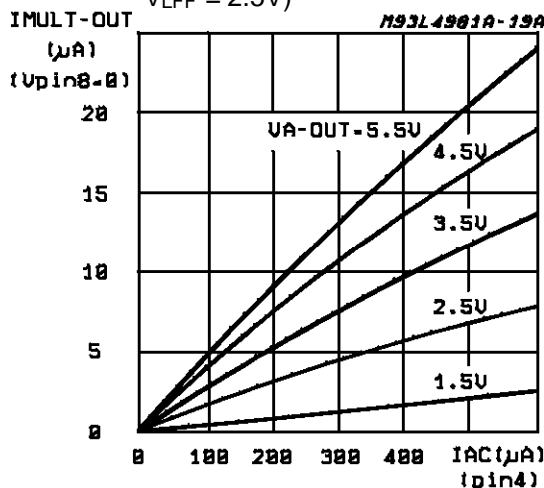


Figure 13h: MULTI-OUT vs. I_{AC} (V_{RMS} = 5.3V; V_{LFF} = 2.5V)



The pin has to be connected through a resistor (R_i') to the negative side of R_s (see fig. 9) to sum the (I_L ζ R_s) and the (I_{mult} ζ R_i') signals. The sum result is the error signal voltage to the current amplifier non inverting input.

$$R_i' \zeta I_{mult} = R_s \zeta I_L$$

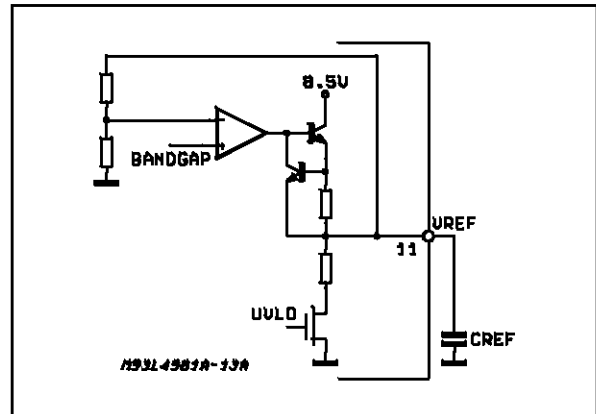
Pin 9. ISENSE (Current Amplifier inverting input). This pin, is externally connected to the external network described at CA-OUT (pin 5). To be noted that R_i and R_i' have the same value because of the high impedance feedback network.

Pin 10. SGND (Signal ground). It has to be connected, to the pc-board GND, close the filtering reference capacitor.

Pin 11. VREF (Voltage reference). An internal

bandgap circuitry, allows an accurate voltage reference. An external capacitor filter (from 100nF to some µF) connected to the signal ground is recommended (see fig. 14). This pin can deliver up to 10mA and can be used for external needs (e.g. enable for other circuits).

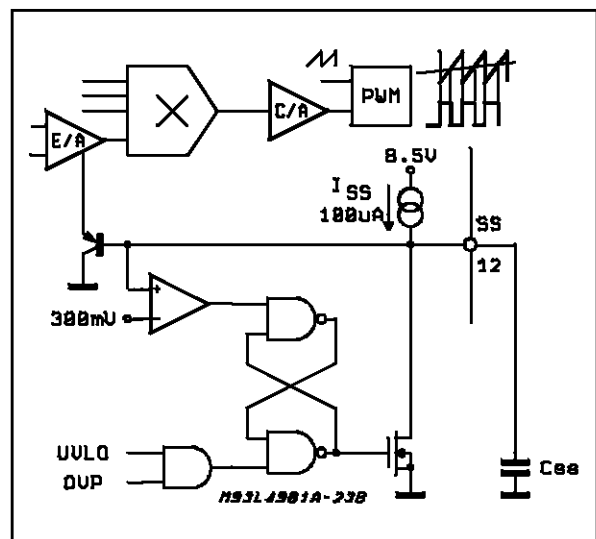
Figure 14.



Pin 12. SS (Soft start). This feature avoids current overload on the external Mosfet (Q) during the ramp-up of the output boosted voltage. An internal switch discharges the capacitor if output overvoltage or VCC undervoltage are detected. An internal current generator of 100µ with the external capacitor define the soft start time constant (see fig. 15). Because the voltage at the softstart pin acts on the E/A output (driving the multiplier with V_{VAOUT} = 5.1V typical voltage swing), the softstart time is defined by:

$$t_{ss} = C_{ss} \zeta \frac{V_{VA\pm OUT}}{I_{ss}}$$

Figure 15.



APPLICATION NOTE

This time (t_{SS}) depends on the application parameters (output voltage, input voltage, output capacitor value, boost inductor size, etc.) and normally the value amounts at some tens of msec.

Pin 13. V_{VA-OUT} (Error amplifier output). Output of the E/A that determinates the control of the boosted regulated voltage (V_O). This pin has to be connected with a compensation network to the pin 14 (see fig.16).

Figure 16.

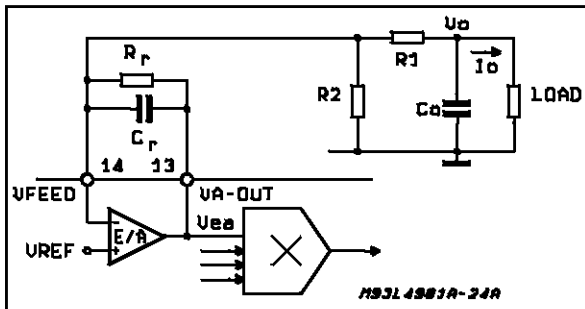
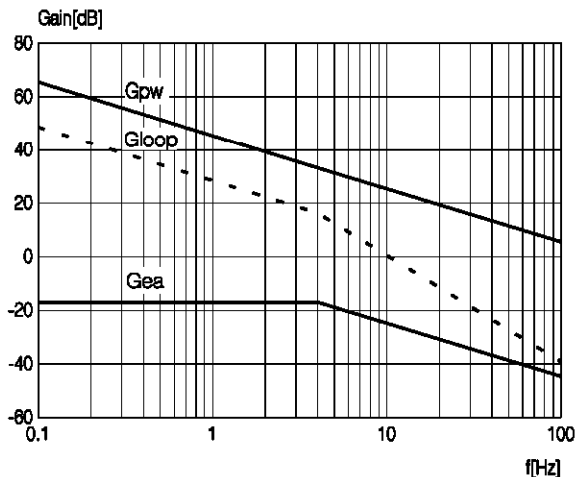


Figure 16a.



First of all, the system does not have to attempt to regulate the twice mains frequency output voltage ripple (ΔV_O) to avoid the line current distortion. Moreover the system stability has to be ensured. The voltage open loop gain can be splitted in two separated blocks.

The first block small signal gain, is given by the ratio between the E/A output voltage (v_{ea}) and output voltage variation (v_o) and is defined by the E/A network:

$$Gea' = \frac{v_{ea}}{v_o} = \frac{1}{s \zeta R_1 \zeta C_r}$$

Where Gea' is the E/A gain without R_r ref. fig. 16. R_2 has no effect on the error amplifier gain be-

cause the inverting input potential is fixed to V_{REF} . The Gea can be seen also as the ratio between the error amplifier output ripple and the imposed output voltage ripple (ΔV_O). The E/A output signal can swing between 1.28V to 5.1V. A value less than 2.5% of the effective E/A output swing voltage ($V_{VAOUT} = 3.82V$) could be chosen to fix the C_r . So, the Gea defined at the output voltage ripple frequency, determinates the C_r value to ensure the 100/120 Hz (2f) attenuation.

$$Gea \approx \frac{0.095 V}{\Delta V_O}$$

$$C_r = \frac{1}{2 \zeta \pi \zeta 2f \zeta R_1 \zeta Gea} \cdot Ka \zeta \frac{\Delta V_O}{R_1}$$

where: $Ka = 1/60$ for 50Hz and $1/72$ for 60Hz mains frequency.

Lower C_r value could increase harmonic distortion. The second block (Power block) is represented by the output filter capacitor (C_O) with its own reactance (X_{CO}), the system has to be able to compensate the total external load variation through the E/A output response (ΔV_{ea}). The power gain transfer function (G_{pw}), for large variations can be written:

$$G_{pw} = I_o \frac{X_{CO}}{\Delta V_{ea}}$$

The total load variation (I_o) to be considered is: $P_{O(max)}/V_O$:

$$G_{pw} = \frac{P_O \zeta X_{CO}}{V_O \zeta \Delta V_{ea}} \% \quad G_{pw} = \frac{P_O}{V_O \zeta \Delta V_{ea}} \zeta \frac{1}{s \zeta C_O}$$

The voltage open loop gain contains two poles in the origin, then stability problem can arise. Connecting the resistor (R_r) in parallel to the capacitor C_r to shift the E/A pole from the origin to $1/(R_r \zeta C_r)$, the stability is ensured.

The crossover frequency f_c can be calculated by $G_{pw} \zeta Gea' = 1$ and therefore:

$$f_c = \frac{1}{2 \pi \zeta C_O} \cdot \frac{P_O}{V_O \zeta \Delta V_{ea}} \cdot \frac{1}{R_r \zeta C_r}$$

To allow the highest DC gain maintaining a phase margin of at least 22° , the R_r maximum value is imposed as:

$$R_r \leq \frac{2.75}{2 \pi \zeta f_c \zeta C_r}$$

The output filter capacitor value (C_O) is related to the output voltage filtering (see Power section design).

Pin 14. V_{FEED} (Error amplifier input). This pin (see fig. 16), connected to the boosted output voltage through a divider, allows the output D.C. voltage regulation. Neglecting the contribution of the E/A

feedback resistor (R_f), the 5.1V reference and the output DC voltage (V_O) define the ratio between R_1 and R_2 :

$$\frac{R_1}{R_2} = \frac{V_O}{5.1V} \pm 1$$

To be considered that the R_1 , together with the feedback network (see pin 13 description) define the E/A gain. The R_1/R_f ratio affects the load regulation (lower output current increases the output voltage) with the following relation:

$$\Delta V_{Omax} = \frac{\Delta V_{ea} \zeta R_1}{R_f}$$

where: V_{Omax} is the maximum output voltage variation due to the E/A gain reduction and load variation.

The R_1 and R_2 will be chosen in the high precision class:

Pin 15. P-UVLO (Programmable supply undervoltage threshold). An internal divider (between pin 19, pin 15 and ground) and an internal comparator with a threshold voltage of 1.28V fixes the default turn-on and turn-off 15.5V and 10V levels of the supply section (see fig. 17). Using an external divider (R_H and R_L) it's possible to change the supply thresholds: R_H fixes the hysteresis, R_L fixes the turn-on threshold. To design a divider for a given supply threshold, is useful know (see fig. 17), the typical resistor value, useful to design the external divider, are: $R_1 = 394k$, $R_2 = 88k$ and $R_3 = 58k$. Anyway, in fig. 17a/b a diagram with threshold values and a table, useful for a fast choice of R_H and R_L are shown.

For DISABLE function see Appendix B.

Pin 16. SYNC (In/Out synchronization). Only for L4981A, this function allows the device to be synchronized with other circuits of a system (see

Figure 18a.

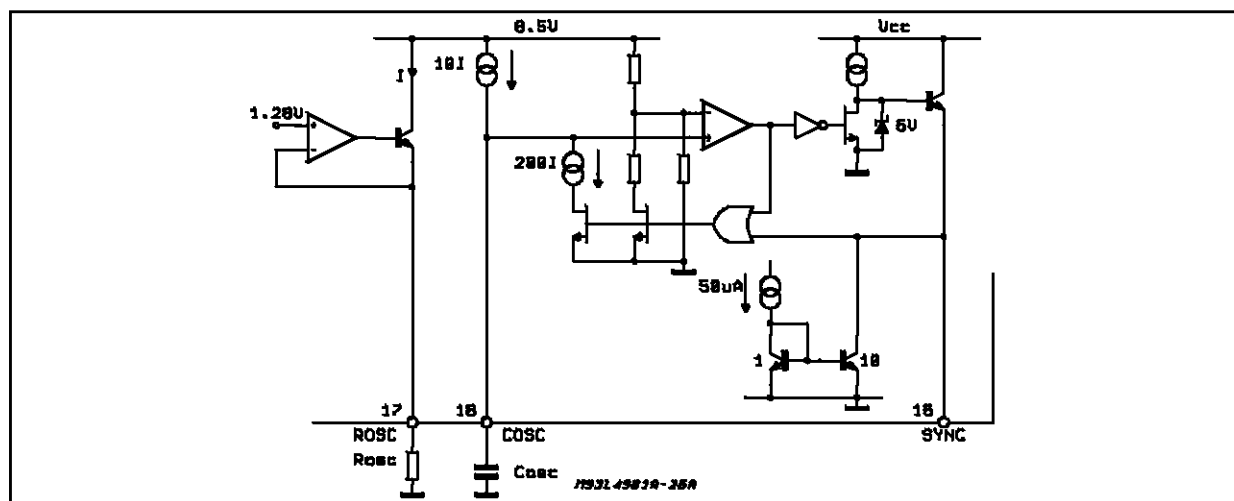


Figure 17: Programmable Under Voltage Lockout Thresholds

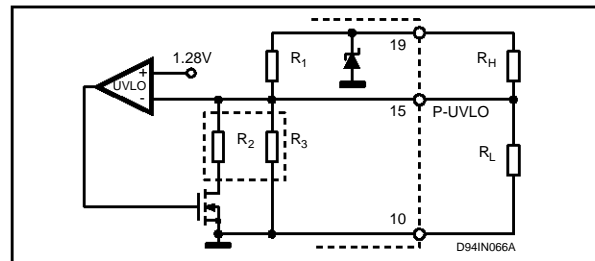


Figure 17a: V_{CCON} and V_{CCOFF} vs. R_L

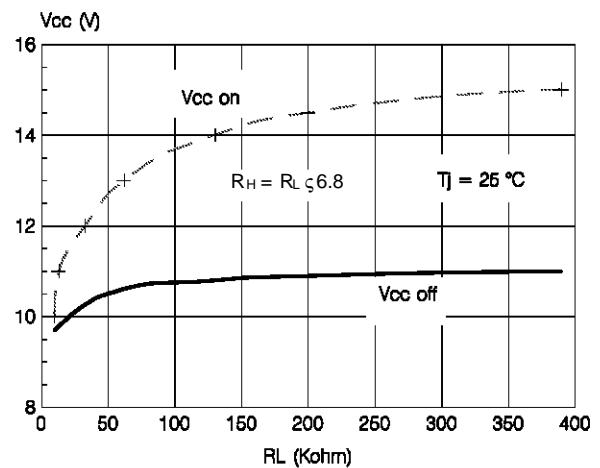


Figure 17b:

$V_{CC ON}$	$V_{CC OFF}$	R_H	R_L
11V	10V	82k Ω	12k Ω
12V	10.1V	220k Ω	33k Ω
13V	10.5V	430k Ω	62k Ω
14V	10.8V	909k Ω	133k Ω
14.5V	10.9V	1.36M Ω	200k Ω
15V	11V	2.7M Ω	390k Ω

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Figure 18b.

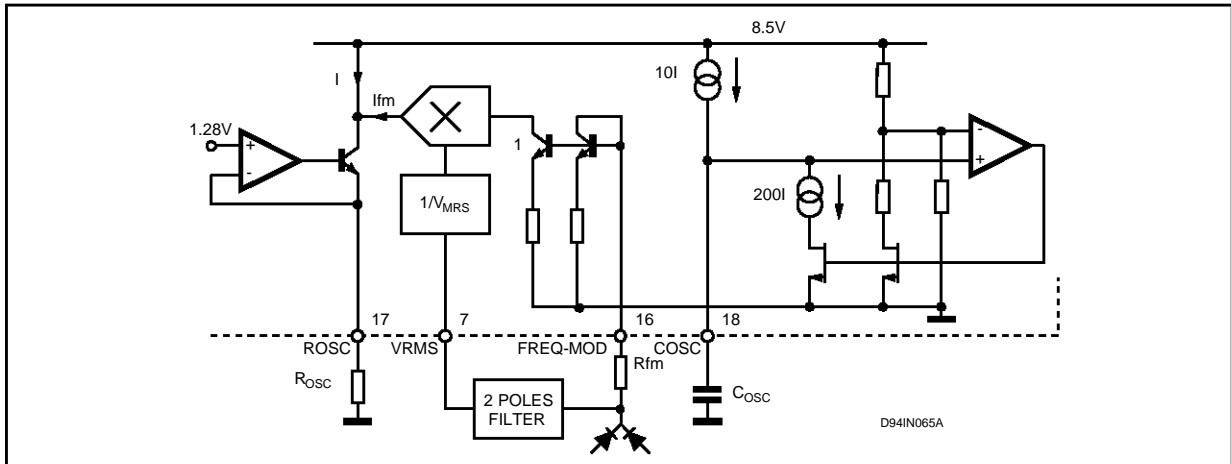


Figure 18c: Modulation Frequency Normalized in an Half Cycle of the Mains Voltage

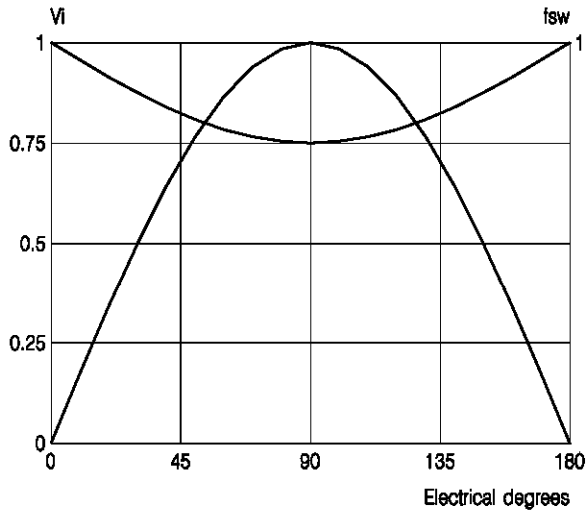


fig.18a). When the device is externally synchronized, the external clock has to satisfy these conditions: the signal amplitude must cross the threshold value (3.5V), the frequency has to be slightly higher than that programmed by the R-C constant (see pin 18) and the pulse width has to be at least 800 nsec.

If the device has to synchronize other circuits, the signal delivered by this pin is a positive pulse of 4.6V (0.5mA) and the pulse duration is equal to the sawtooth falltime.

The L4981B uses this pin to perform another function. If the application does not use the SYNC function, it is preferable to focus the EMI filtering problem using the B version. Pin 16, named FREQ-MOD in B version, allows to change the switching frequency in order to spread the energy content over a wider spectrum range.

To perform the frequency modulation (see fig.18b), the pin must be connected, through a re-

sistor (R_{fm}), to the rectified line voltage. This allows to change dynamically (cycle by cycle) the (C_{osc}) charge and the discharge currents that define the ramp slopes of the oscillator sawtooth. The effect of the resistor produces the frequency change (see fig.18c) between the nominal value (f_{sw}) and its minimum value which occurs when the input voltage reaches the peak value (V_{ipk}). The total frequency variation (see also pin 17 and 18) can be estimated by the formula:

$$\frac{\Delta f_{sw}}{f_{sw}} = K \frac{V_{IPK} \zeta R_{osc}}{V_{RMS} \zeta R_{fm}}$$

where: R_{fm} is the programming current resistor.
K is a constant value = 0.1157 for R value in $K\Omega$ and f_{sw} in KHz.

A typical 20% $\frac{\Delta f_{sw}}{f_{sw}}$ can be a good compromise.

Pin 17. ROSC (Oscillator resistor). An external resistor connected to ground, programs the charge and the discharge currents that pin 18 (C_{osc}) forces to the external capacitor. The reference voltage at pin 17 is 1.28V (see fig.18a/b)

To set the charge current, the relation is:

$$I_c \approx 10 \zeta \frac{1.28V}{R_{osc}}$$

The discharge current is defined by:

$$I_d \approx 200 \zeta \frac{1.28V}{R_{osc}}$$

The maximum discharge current of $I_d = 12mA$, this means a minimum R_{osc} value of $22K\Omega$.

Pin 18. COSC (Oscillator capacitor). An external capacitor (see fig 18a/b), connected between this pin and ground, fixes the rise and fall time (t_r and t_f) of the sawtooth oscillator according to the pre-

vious relations (pin 17) and therefore the switching frequency. The typical ramp valley-peak voltage (V_{srp}) is fixed to 5V.

The period T is defined by:

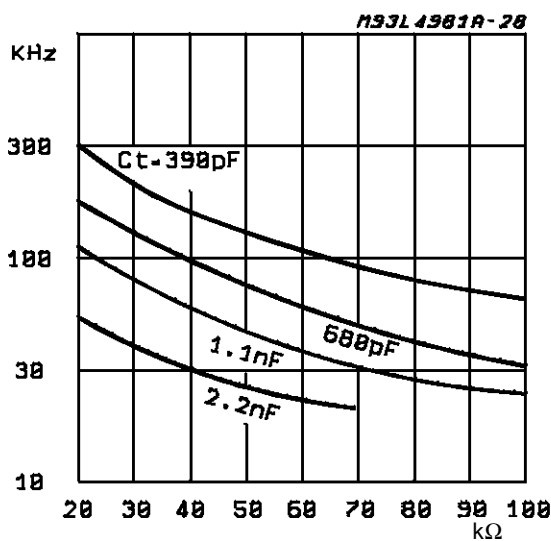
$$T = t_r + t_f = V_{srp} \zeta C_{osc} \left(\frac{T1}{V_{IC}} + \frac{1}{I_{d<}} M \right)$$

the switching frequency is:

$$f_{sw} = \frac{1}{T} \approx \frac{2.44}{R_{osc} \zeta C_{osc}}$$

See also Fig. 19

Figure 19: Oscillator Diagram



Pin 19. VCC (Supply voltage input). The very low current consumption feature before the turn-on threshold is reached. The undervoltage circuitry, with the threshold hysteresis of 5.5V typ. (see also pin 15) and an internal clamp at 25V (typ.) ensure the IC safety operation.

Pin 20. GDRV (Gate driver output). This output is internally clamped to 15V (see Fig. 20), to avoid ageing problems of the gate oxide. The output driver is normally connected to the gate of the power device through a resistor (say 5 to 50 Ohm) to avoid overshoot and to control the di/dt of the switch.

POWER SECTION DESIGN

Booster Inductor

The Boost Inductor design involves various parameters to be handled and there are different approaches to define them.

In continuous mode operation, the energy stored in the boost inductor in each switching cycle, is

Figure 20.

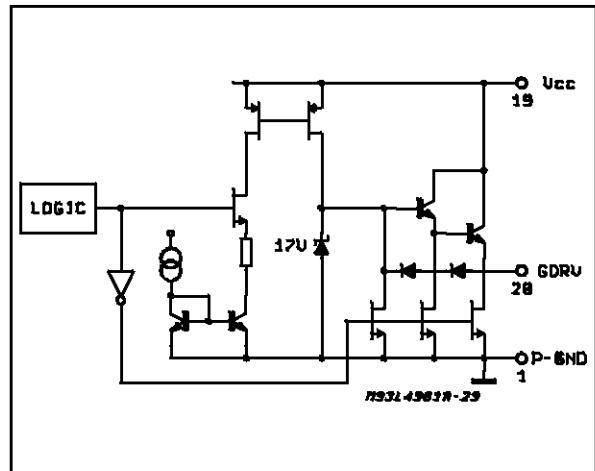
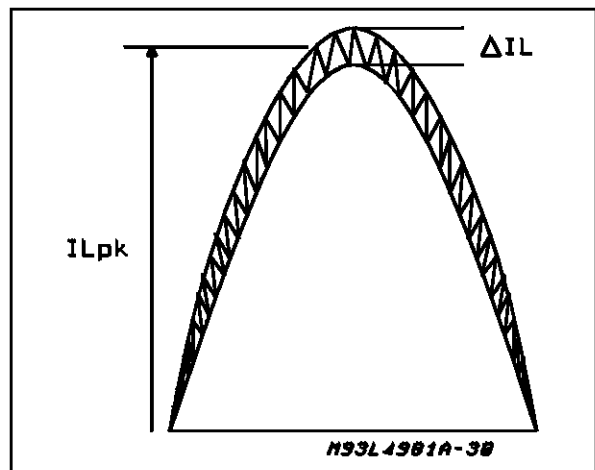


Figure 21.



not completely transferred to the output (bulk) capacitor. A quantity of energy is stored in the magnetic circuit, reducing in this way the input current ripple. This minimizes the line noise and reduces the input filter size (see fig.21).

The energy transferred from the boost inductor to the bulk capacitor in each cycle is:

$$E_{cycle} = \frac{1}{2} L \zeta (I_{Lp}^2 \pm I_{Lv}^2) = L \zeta I_{Lt} \zeta \Delta I_L$$

where:

- L = Boost Inductance
- I_{Lp} = Inductor Peak Current ($I_{Lt} + \Delta I_L/2$)
- I_{Lv} = Inductor Valley Current ($I_{Lt} - \Delta I_L/2$)
- I_{Lt} = Instantaneous Line Current $(I_{Lp} + I_{Lv})/2$
- ΔI_L = Twice Inductor Current Ripple ($I_{Lp} - I_{Lv}$)

Because the instantaneous line current (I_{Lt}) that corresponds to the average inductor current in the

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cycle, draws a full rectified (half- sinusoidal) waveform, it is useful to refer to the AC line RMS and peak parameters:

$$I_{Lpk} = \sqrt{2} \zeta I_{Lrms}$$

where: $I_{rms} = I_{Lrms} = P_i/V_{rms}$ is the line current
 $P_i = P_o/\eta$ is the input power
 η is the power yield.

The power transferred by the inductor in each cycle

$$P_t = \frac{L \zeta I_{Lt} \zeta \Delta I_L}{t_{on}}$$

where: $t_{on} = \delta / f_{sw}$ and $\delta = (V_o - V_{it}) / V_o$

For a given L, the twice ripple current ΔI_L is the quantity associated to the transferred energy and can be calculated as a certain percentage of the I_{Lpk} inductor current.

$$\Delta I_L = \frac{V_{it} \zeta (V_o \pm V_{it})}{V_o \zeta f_{sw} \zeta L}$$

If the maximum V_{ipk} value is higher than the $V_o/2$,

the maximum ΔI_L occurs when $V_{it} = \frac{V_o}{2}$ and its

value is $\Delta I_{L(max)} = \frac{V_o}{4 \zeta f_{sw} \zeta L}$.

If the V_{ipk} maximum value does not reach $V_o/2$ voltage value, the maximum ΔI_L is reduced and its value is :

$$\Delta I_{L(max)} = \frac{V_{ipk} (V_o \pm V_{ipk})}{V_o \zeta f_{sw} \zeta L}$$

In continuous mode approach, the acceptable current ripple level (K_r) can be considered between 10% to 35%.

$$K_r = \frac{\Delta I_L}{2 \zeta I_{Lpk}}$$

Smaller current ripple on the inductor involves smaller noise on the rectified main bus reducing the input filter size; but the ripple reduction will impose an increase of the boost inductor.

The high voltage, the flux density and the frequency range make the standard high frequency ferrite the most useful material in P.F.C. applications. To avoid the core saturation, related to the high permeability materials, it is necessary built an air-gap in order to allow an adequate magnetic force range ($H+H_{gap}$).

An easy approach, is to have an approximated minimum value of core size that could be used to perform the conversion:

$$\text{Volume} \cdot K \zeta L \zeta I_{Lpk} \zeta \Psi_{Lpk} + \frac{\Delta I_L N}{2} M <$$

where : K = specific energy constant.

L = Boost inductor value in H.

The specific energy constant (K), mainly depends on the ratio between the gap length (l_{gap}) and the effective length (l_{eff}) of the magnetic core set and on the maximum ΔB swing. Practically

$$K \approx 14 \zeta 10^{\pm 3} \frac{l_{eff}}{l_{gap}}$$

can be used to get the minimum volume of the core set in cm^3 . After the minimum core-set size is estimated, the suitable type will be selected with technical and economic evaluations.

Next step will be the design of the coil parameters.

The above mentioned formula $P_{Ot} = \frac{L \zeta I_{Lt} \zeta \Delta I_L}{t_{on}}$

if referred to the magnetic path, can be rewritten :

$$P_{Ot} = Ae \zeta l_{eff} \zeta H \zeta \frac{\Delta B}{t_{on}}$$

where : Ae = effective area of the core section.

l_{eff} = effective magnetic path length.

ΔB = deviated magnetic flux density.

H = magnetic field strength.

The ratio between the ferrite and the air path magnetic permeability, depends on the ferrite materials. Core materials for power application (such as B50/51), have a initial permeability value about 2500 times that of air. This means that, above a certain air-gap length percentage, it is possible to neglect the l_{eff} (length of the core) simplifying the calculation e.g. if a 1% of air-gap length, respect to the core length value is used, the error introduced is about 4%.

Rewriting $P_{Ot} = Ae \zeta l_{eff} \zeta H \zeta \frac{\Delta B}{t_{on}}$

$$P_{Ot} \approx Ae \zeta l_{gap} \zeta H_{gap} \zeta \frac{\Delta B}{t_{on}}$$

equating to and simplifying $P_{Ot} = \frac{L \zeta I_{Lt} \zeta \Delta I_L}{t_{on}}$

$$Ae \zeta l_{gap} \zeta H_{gap} \zeta \Delta B \approx L \zeta I_{Lt} \zeta \Delta I_L$$

Because: $l_{gap} \zeta H_{gap} \approx N \zeta I_{Lt}$ and $\Delta B = \mu_0 \zeta \Delta H$

$$Ae \zeta N \zeta \mu_0 \Delta H \approx L \zeta \Delta I_L$$

$$\Delta H \approx N \frac{\Delta I_L}{l_{gap}}$$

and finally:

$$N \approx \frac{L \zeta I_{gap}}{\mu_0 \zeta Ae}$$

This simplified relation is much easier to use than the complete one:

$$N \geq \frac{L I_{\text{gap}}}{\mu_0 \sum \frac{1}{\Delta Y} + \frac{\pi}{4} \zeta I_{\text{gap}} M} + \frac{I_{\text{eff}}}{\mu_r \zeta A_e} >$$

After N has been defined, it's necessary to check the core for saturation of the magnetic path (rated $N \zeta I_{\text{max}}$ vs. Air-gap on ferrites databook). If the check is too close the rated limit, an increase of the I_{gap} (gap length) and a new calculation will be necessary. Copper losses $R_L \zeta I_{\text{Lrms}}^2$ and former's winding space available will be considered for the wire selection.

An auxiliary winding can be used just to get a low cost supply for the I.C. It will be a low cost thin wire coil will be used and the number of turns is the only parameter to define.

Input Bridge

The input diodes bridge can be standard off-line, slow-recovery and low cost devices. The device selection considers just the input current (Irms) and the thermal data.

Input Capacitor

The input filter capacitor (C_{IN}) has to sustain the input instantaneous voltage (V_{it}), with an imposed voltage ripple, during the turn-on (t_n) time of the Mosfet.

The worst conditions will be found at the minimum rated input voltage $V_{Irms(\text{min})}$.

The maximum high frequency voltage ripple ($r = \Delta V_I / V_I$) has to be imposed:

$$C_{IN} \cdot K_r \frac{I_{rms}}{2 \zeta \pi \zeta f_{sw} \zeta r \zeta V_{Irms}}$$

Where: K_r is the current ripple coefficient.
 $r = 0.02$ to 0.08 .

The C_{IN} maximum value is limited to avoid current distortion.

Output Bulk Capacitor

The choice of the output bulk capacitor (C_O), mainly depends on the electrical parameters that affect the filter performances and also on the subsequent application.

The D.C. output voltage and overvoltage, the output power and voltage ripple are the first parameters to consider in all applications. The RMS capacitor ripple current $I_{C(2f)rms} = I_o / \sqrt{2}$ and so, the output voltage ripple (ΔV_O) will be:

$$\Delta V_O = I_o / \sqrt{\frac{1}{(2 \pi \zeta 2f \zeta C_O)^2} + (ESR)^2}$$

With a low ESR capacitor can be simplify:

$$C_O = \frac{I_o}{2 \pi \zeta 2f \zeta \Delta V_O} = \frac{P_o}{2 \pi \zeta 2f \zeta \Delta V_O \zeta V_O}$$

Although the ESR, normally does not affect the output ripple parameter, it has to be considered in power losses account both for the rectified mains frequency and the switching frequency.

If the application (i.e. computer supply) has to guarantee a specified Hold-Up time (t_{HOLD}), the capacitance sizing criteria will change:

The C_O has to deliver the supply energy for a certain time and a specific dropout voltage.

$$C_O = \frac{2 \zeta P_O t_{\text{HOLD}}}{V_{O_min}^2 \pm V_{op_min}^2}$$

where: V_{O_min} = minimum output voltage value (normally at the maximum load conditions)

V_{op_min} = minimum output operative voltage before the 'power fail' detection.

Power Switch

A power MOSFET is the active switch used in most application for its frequency features. It will be selected according with the output boosted voltage and the delivered power. There are two contributions for power losses in the mosfet: conduction losses and switching losses. The on-state power losses can be calculated using the formula:

$$P_{\text{on-MOS}} = I_{Qrms}^2 R_{dson}$$

One estimation of the switching losses can be done considering two separated quantities:

$$P_{\text{capacitive}} \geq \frac{1}{2} \zeta C_{\text{oss}} \zeta V_o^{1.5} + \frac{1}{2} C_{\text{ext}} \zeta V_o^2 N f_{sw} \zeta$$

$$P_{\text{crossover}} \geq V_O \zeta I_{rms} \zeta t_{cr} \zeta f_{sw} + P_{\text{rec}}$$

where: C_{oss} is the Drain capacitance at $V_{DS} = 25V$.
 t_{cr} is the crossover time.

C_{ext} is the external layout stray capacitance.

P_{rec} is the contribution due to the diode recovery.

To reduce the crossover losses a snubber network can be used.

Booster diode

The booster diode will be selected to withstand the output voltage and current. Moreover, it has to be as fast as possible in order to reduce the power switch losses.

The SGS-THOMSON Turboswitch] diode series match this specifications, and are especially suitable for this application.

The diode power losses can be split in two contri-

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Contributions: conduction losses and switching losses. The conduction losses can be estimated by:

$$P_{Don} = V_{to} \zeta I_O + R_d \zeta I_{Drms}^2$$

where: V_{to} = threshold voltage

R_d = differential resistance

Sense Resistor

The sense resistor produces the signal for the current feedback loop and for the overcurrent protection circuit.

An easy criterion to choose the sense resistance is to minimize the power dissipated assuring a sufficient signal to noise ratio.

A PRACTICAL EXAMPLE

The following PFC design example is referred to the evaluation board, realized for demonstration purpose.

The design target specification are:

- UNIVERSAL AC input supply voltage
 $V_{rms} = 88V$ to $264V$
- DC output regulated voltage $V_O = 400V$
- Rated output power $P_O = 200W$
- Full load output ripple $\Delta V_O = + 8V$
- Maximum overvoltage value $\Delta V_O = 50V$
- Switching frequency $f_{sw} = 100kHz$
- Maximum Inductor current ripple $\Delta I_L = 35\%$ of I_{Lrms}
- Worse condition efficiency (at minimum input voltage) $\eta = 90\%$

To match the specifications the material selection, especially for some critical components is an important step. The choice criterion for some of this components is here described.

Power Mosfet:

Since the Mosfet device has to sustain a minimum blocking voltage value of $500V$ ($V_{DSS} = V_O + \Delta V_{OUT} + V_{marg}$), then the most important parameter for the selection is the R_{DSON} for its relation with the power dissipation.

The device $STH15NA50FI$ (or equivalent) with its $500V$ V_{DSS} and the R_{DSON} ($R_{DSON} = 0.4\Omega$ @ $T = 255C$) of about 0.8Ω at $T_j = 1005C$, is a good choice for the application. We can estimate its performance in this application.

-The maximum "on state" power dissipation evaluated at the minimum input mains voltage (see the above formulae) is:

$$P_{on-MOSmax} = I_{Qrms}^2 \zeta R_{on} = 2.15 \zeta 0.8 \zeta 3.7W.$$

- The switching (on + off) losses can be estimated as:

$$P_{crossover} \approx t_{cr} \zeta V_O \zeta f_{sw} \zeta I_{rms}$$

To take into account the booster diode recovery effect, an easy approach is to compute two times the current value (at turn-on), this means 1.5 times the above value:

$$P_{crossover} \approx 1.5 \zeta 40ns \zeta 400V \zeta 100kHz \zeta 2.53A = 6W$$

The capacitive losses at turn-on to be added are:

$$P_{capacitive} \approx \frac{T}{Y} \zeta C_{oss} \zeta V_o^{1.5} + \frac{1}{2} C_{ext} \zeta V_o^2 \zeta f_{sw} = 4W.$$

To reduce the switching losses a voltage snubber (RCD) has been used.

Booster Diode:

Because of the continuous inductor current mode, the Mosfet has to recover the booster diode minority-carrier at turn on. This makes advantageous the choice of an ultra fast recovery time diode. The SGS-THOMSON TurboSwitch family offers the best solution for this kind of application. The STTA506D has been selected to match the board parameters. Considering the frequency of the application and the fast performance of the diode, its power dissipation is mainly due to the conduction losses:

$$P_D = V_{TO} \zeta I_b + R_d \zeta I_{drms}^2 = 1.15V \times 0.5A + 0.07\Omega \times 1.28A^2 = 0.7W$$

Where: V_{TO} and R_d are the diode parameters.

Booster Inductor:

The inductor design starts defining the minimum L value to limit the high frequency ripple current ΔI_L (for the given frequency), under the rated value. It results a minimum inductance of $0.7mH$ ($0.75mH$ has been imposed). Using a gapped ferrite the minimum volume needed is about $6.7cm^3$. So the core set $B1ET3411A$ ($7.5cm^3$) has been selected; its effective magnetic path length = $79mm$ define a gap of $1.4mm$ placed in the central leg to reduce the magnetic radiation, while its effective core area = $97mm^2$ and considering a ΔB up to $250mT$, defines the number of the primary winding = 75 turns.

To minimize the copper losses (skin and proximity effect), a multiwire solution with a bunch of 20 wires of 32 AWG ($0.2mm$) has been used. The maximum resistive copper losses can be calculated with the formula:

$$P_{CU} = I_{Lrms}^2 \zeta R_{CUdc} + I_{Lhfrms}^2 \zeta R_{CUhf} = 1.4W$$

where: $R_{CUdc} = 170m\Omega$ (at $1005C$),

$R_{CUhf} = 5.1\Omega$ (at $100kHz$),

$I_{Lrms} = 2.5A$,

$I_{Lhfrms} = 2.5A \zeta 0.35 / \sqrt{12} = 0.25A$

Output Filter Capacitor:

For the output capacitor (C_O), in this application, the output voltage ripple is the parameter considered. A $100\mu\text{F}/450\text{V}$ has been chosen obtaining a full load ripple voltage of $+8\text{V}$.

Input Filter Capacitor:

To smooth the high frequency ripple, a capacitor of 220nF across the rectified mains (bridge output) has been used. This capacitor allows the demoboard works well. In normal application an EMI filter is interposed between the mains and the PFC circuit. The EMI filter design is not described in this paper, anyhow it is used in the following evaluation.

Sense Resistor:

The parallel of three metal film resistors (0.22Ω), has been used to obtain the resistance of

$R_S = 73\text{m}\Omega$ that gives a good signal level, with a maximum power dissipation:

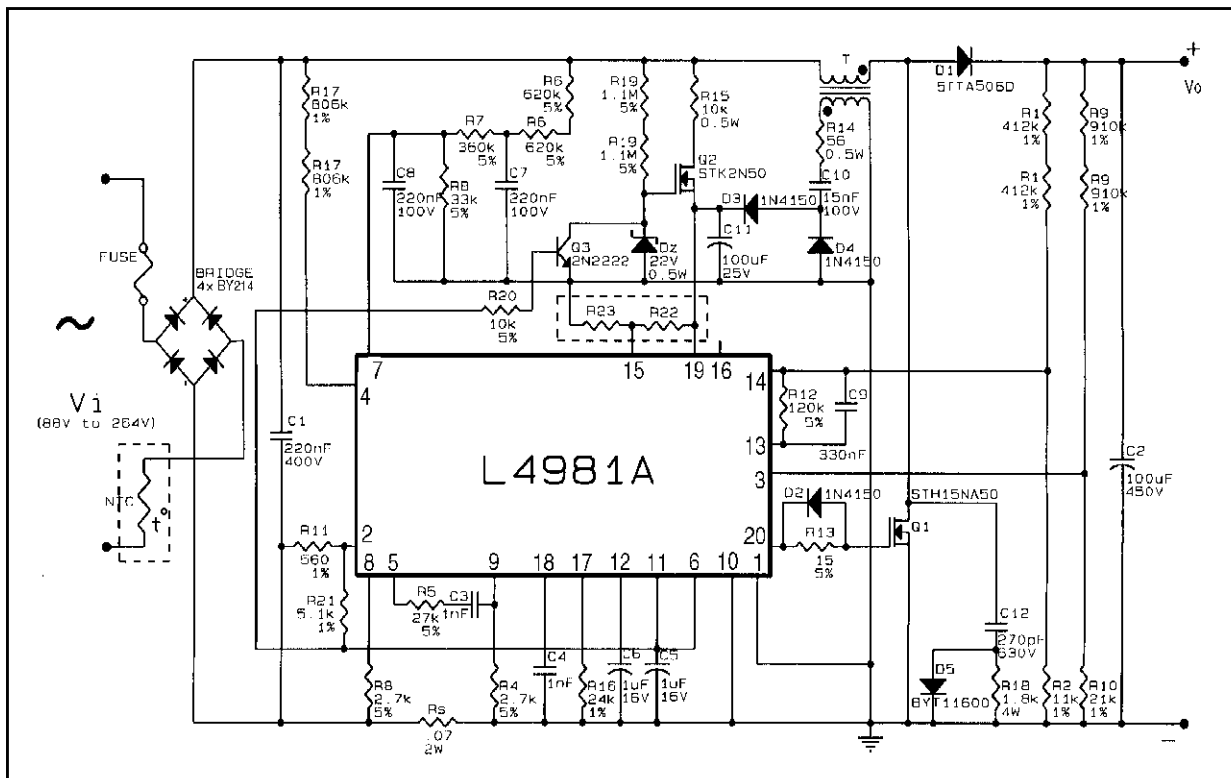
$$P_{R_S} = R_S(I_{L_{rms}}^2 + I_{L_{hfrms}}^2) = 0.46\text{W}$$

Supply Circuit:

To have a stand alone working demoboard, an IC supply circuitry has been added. This circuitry has been designed for a fast start-up and low power consumption. The start-up is realized with Q_2 , Q_3 , D_Z , R_{15} , R_{19} , R_{20} and is turned-off by the V_{REF} signal after the turn-on threshold has been reached. At running the supply, delivered by an auxiliary winding on the booster inductor, is optimized to work with large load variation; anyway if the output power (P_O) goes under 10W this circuit doesn't work well and instability can happen. To work at so low power a different supply solution has to be used.

The other components has been designed with the criteria already described in this paper and their values are reported in the schematic.

Figure 22: 200W Evaluation Board Circuit.



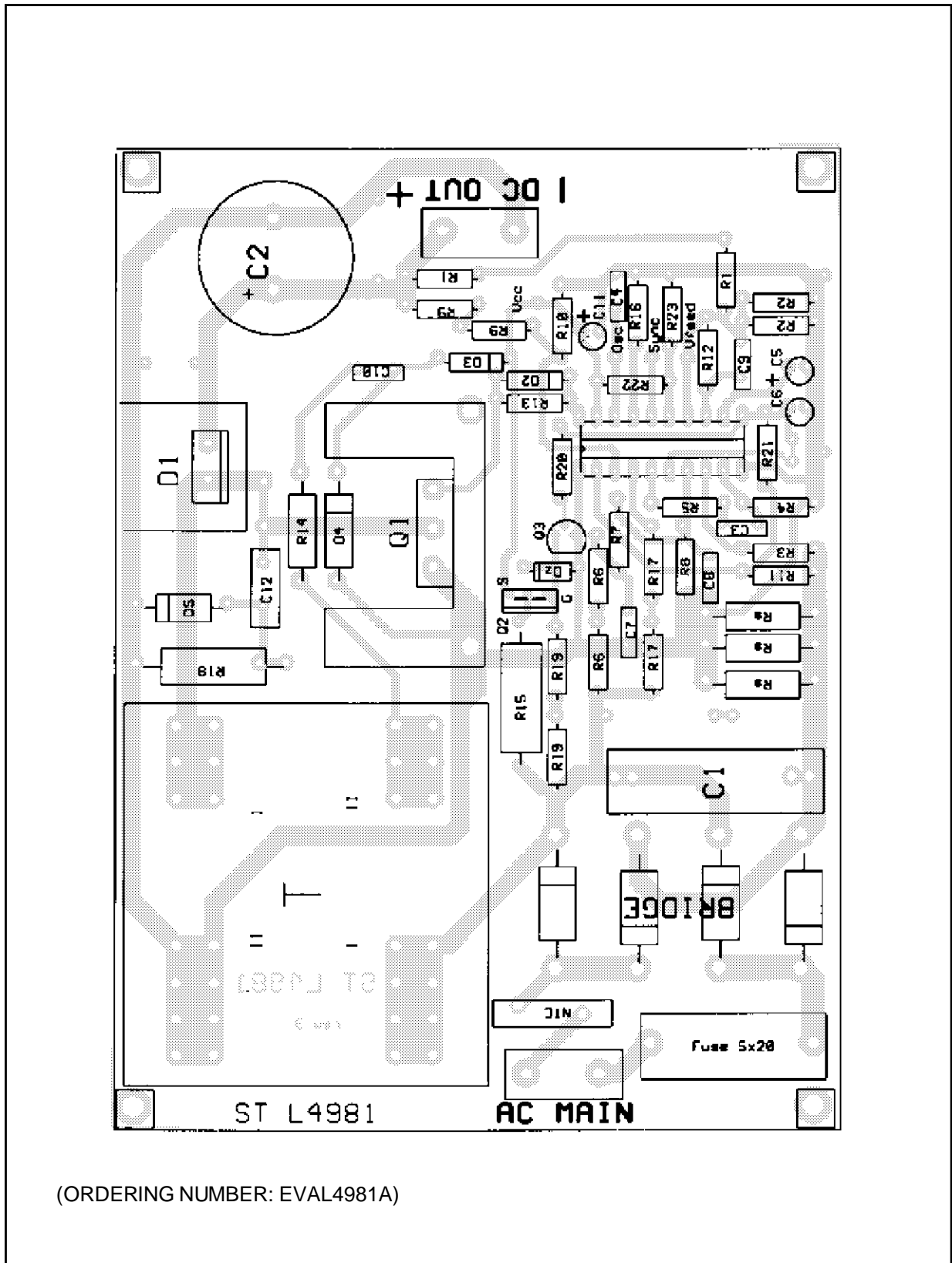
T= primary: 75 turns of litz wire 20 x 32 AWG (0.2mm)
 secondary: 8 turns of # 32AWG (0.20mm)
 core: B1ET3411 A THOMSON- CSF
 gap: 1.4mm for a total primary inductance of 0.7mH

Ref. also OREGA P.N. 473201 A9

$f_{sw} = 100\text{kHz}$
 $V_O = 400\text{V}; P_O = 200\text{W}$

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Figure 23: P.C. Board and Component Layout of Evaluation Board Circuit (1:1 scale)



EVALUATION RESULTS

The evaluation board has been designed using a fast not dissipative start-up circuit (Q2, Q3, R19, R20) even if a simple one could be used and a Turn-off snubber to reduce the MOS power dissipation. The fig. 24 and fig. 25 show the Turn-on and the Turn-off MOS waveform.

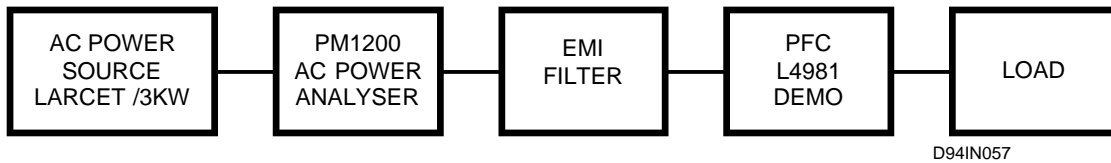
Further there is a possibility to change the input threshold voltage using an external divider (R23 and R22) and if an inrush current problem arises

a NTC resistor could be used.

The PFC demoboard performance has been evaluated testing the following parameters:

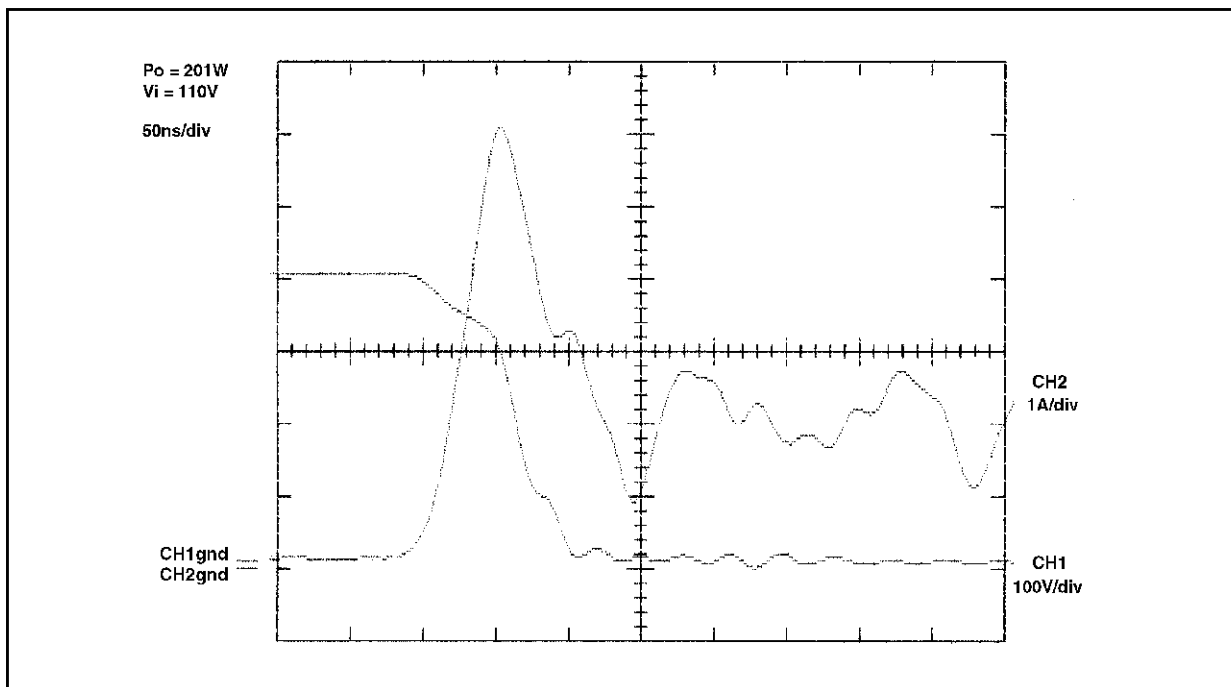
PF (power factor), A-THD (percentage of current total harmonic distortion), H3..H9 (percentage of current's nth harmonic amplitude), ΔV_o (output voltage ripple), V_o (output voltage), η (efficiency).

The test configuration, equipment and results are shown below:



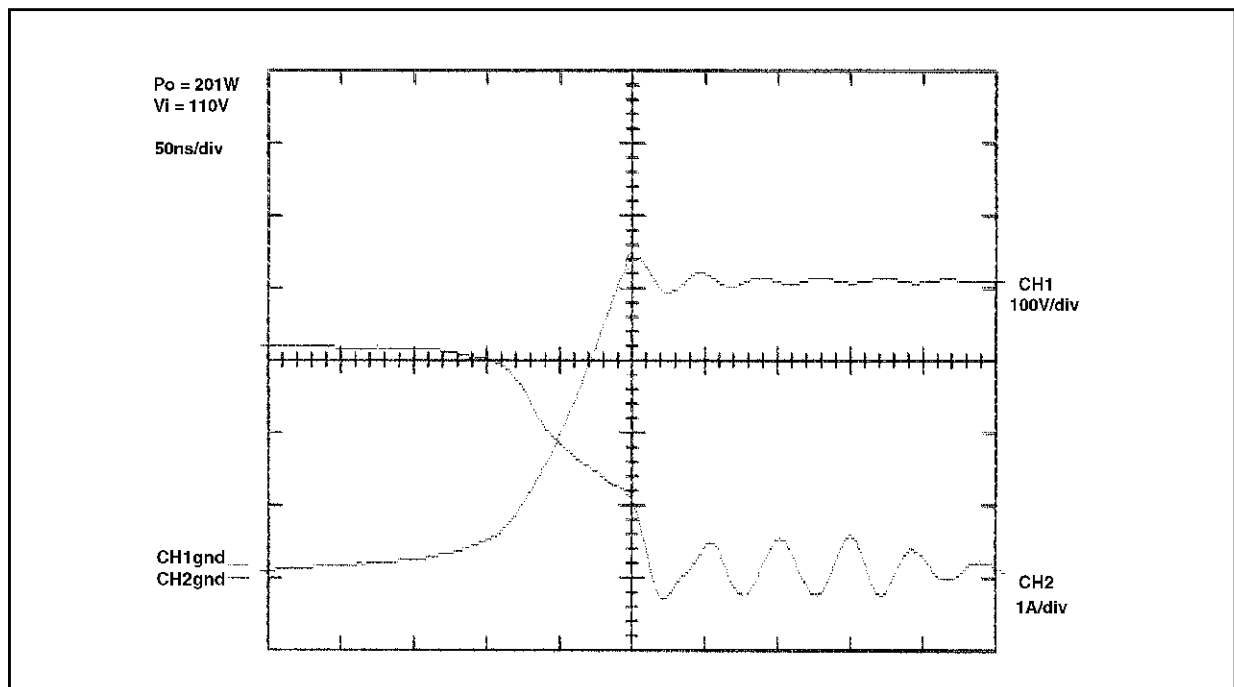
V_i	f	P_i	PF	A-THD	H3	H5	H7	H9	V_o	ΔV_o	PO	η
(V _{rms})	(Hz)	(W)		(%)	(%)	(%)	(%)	(%)	(V)	(V)	(W)	(%)
88	60	222	0.999	2.94	1.98	0.61	0.55	0.70	390	8	200	90.2
110	60	220	0.999	1.79	1.40	0.40	0.31	0.28	392	8	201	91.6
132	60	218	0.999	1.71	1.16	0.40	0.35	0.31	394	8	202	92.8
180	50	217	0.999	1.88	1.52	0.65	0.40	0.34	396	8	203	93.8
220	50	217	0.997	2.25	1.68	0.83	0.57	0.48	398	8	204	94.2
260	50	216	0.995	3.30	1.84	1.30	0.39	0.73	400	8	205	95.2

Figure 24: Turn-on Switch.



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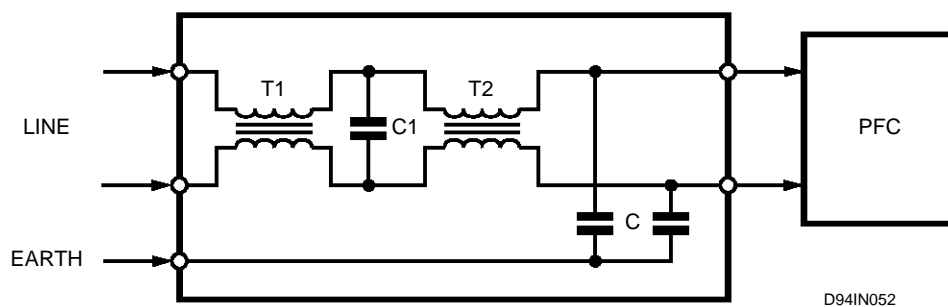
Figure 25: Turn-off Switch.



EMI/RFI FILTER

The harmonic content measurement has been done using an EMI/RFI filter interposed between

the AC source and the demoboard under test, while the efficiency has been calculated without the filter contribution.



Where:

T1 = 1mH C1 = 0.33 μ F, 630V
T2 = 27mH C2 = 2.2nF, 630V

APPENDIX A

LFF (pin 6) Function.

Since in Power Factor applications the Error Amp. compensation network has to filter the mains frequency contents, in order to reduce harmonic distortions, the crossover frequency of the loop gain must be low. This involves a poor load transient response.

An additional function (LFF) is available in L4981A/B devices. It is especially suitable to modify the multiplier output current, proportionally to the load, in order to improve the system response by bypassing the E/A. The control is working with VLFF voltage between 1.5V and 5.1V.

In fig. A1 is shown an application example to explain this function. An external OP-AMP has been used to get the suitable signal voltage avoiding sense resistor (R1) power dissipation.

In the real application the sense resistor is often replaced by sense transformer.

Design criteria:

It is necessary to ensure a minimum VLFF = 1.6-1.7V at the minimum output current. Since the OP-AMP (LM258) $V_{ol} = 0.7V$ (@ 1mA), to get the minimum voltage at VLFF, 1V has to be added. A resistor divider tied to the reference voltage (pin 11 of the controller) shifts the output of the OP-AMP.

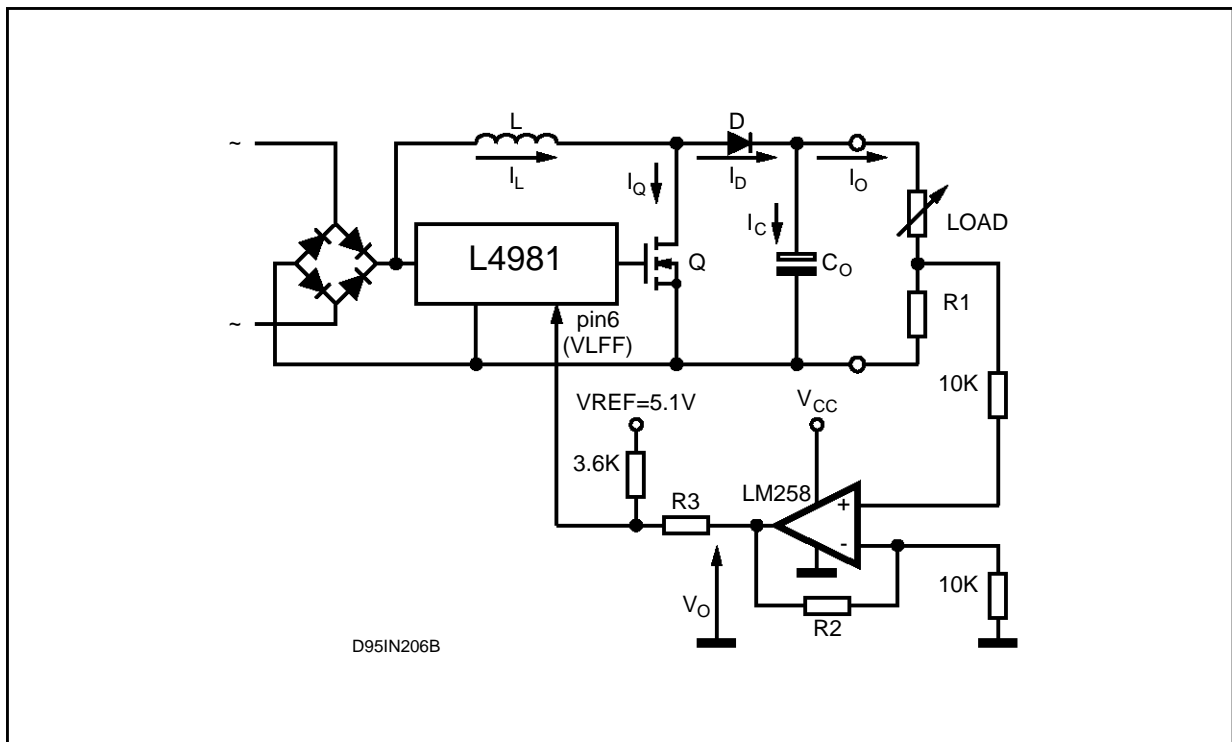
$$\text{therefore } 1V = \frac{(5.1V \pm 0.7V)}{R3 + 3.6k\Omega} \cdot R3 \quad \% \quad R3 = 1k\Omega$$

The OP-AMP supply voltage is the same used for PFC controller (V_{CC}) and its gain is fixed in order to produce $V_o = 5.1V$ at the maximum load ($I_{o \max}$).

$$V_o = R1 \cdot I_{o \max} \cdot \frac{1}{10k} + \frac{R2 \cdot V_{REF}}{10k} = 5.1V$$

E.g. for $I_{o \max} = 3A$. $R1 = 0.1\Omega$ - 1W $R2$ is roughly 160K Ω .

Figure A1: Application example.



APPLICATION NOTE

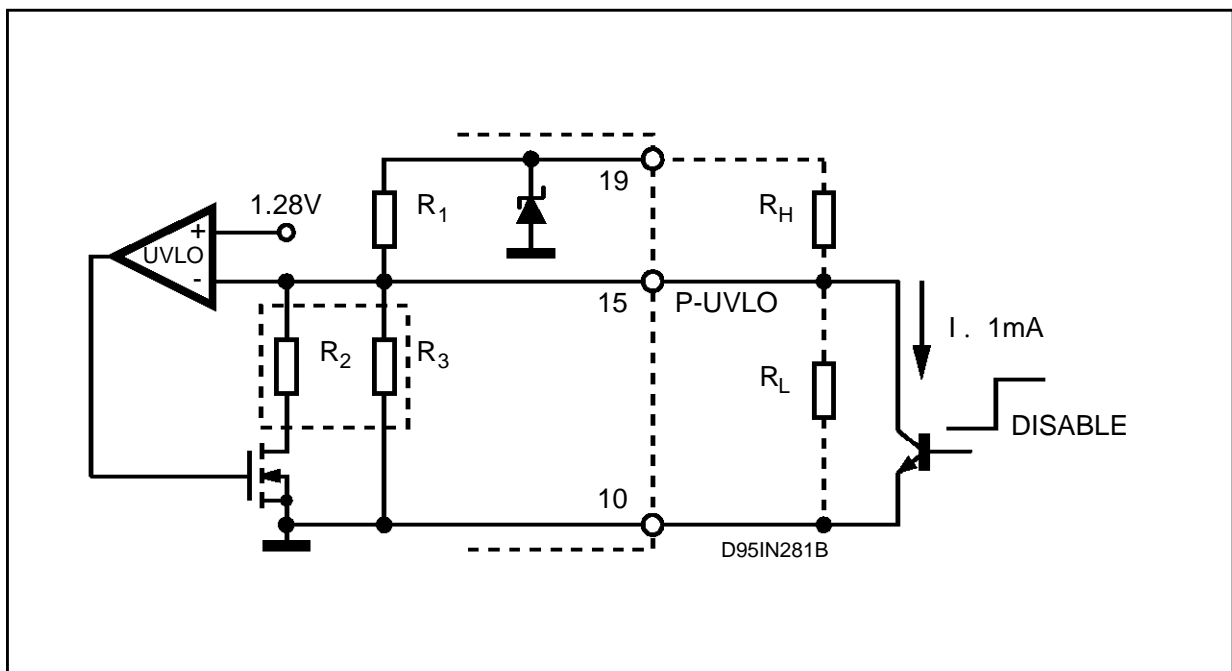
APPENDIX B

Disable

Sometimes it is useful to disable the controller. For example, in a complete system in which a PWM regulator follows the PFC stage, at low output power it is advantageous to shutdown the PFC section to improve the overall system efficiency (stand-by / sleep mode). Likewise most of controllers, one way to do this (using L4981 A/B), is pulling down either the Soft-Start or the E/A output pin. In addition the L4981 A/B can be disabled grounding the P-UVLO (pin 15) see fig B1.

The P-UVLO function has been designed to program the supply thresholds by means of an external divider (see application note for details) but it can be effectively used for this purpose forcing a voltage below the internal reference (1.28V). Besides turning off the driver output stage this method puts the controller in "before start-up" condition and gives the advantage of minimizing the supply consumption of the IC.

Figure B1.



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